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Autore	Liu Cheng-Hua
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Nota di contenuto	Introduction -- Theoretical background -- Experimental methods -- Distinctive magnetotransport of graphene p-n-p junctions via resist-free fabrication and controlled diffusion of metallic contact -- Observation of quantum Hall plateau-plateau transition and scaling behavior of the zeroth Landau level in graphene p-n-p junction -- Extrinsic Origin of Persistent Photoconductivity in Monolayer MoS2 Field Effect -- Conclusion.
Sommario/riassunto	This thesis focuses on the transport and magneto-transport properties of graphene p-n-p junctions, such as the pronounced quantum Hall effect, a well-defined plateau-plateau transition point, and scaling

behavior. In addition, it demonstrates persistent photoconductivity (PPC) in the monolayer MoS₂ devices, an effect that can be attributed to random localized potential fluctuations in the devices. Further, it studies scaling behavior at zeroth Landau level and high performance of fractional values of quantum Hall plateaus in these graphene p-n-p devices. Moreover, it demonstrates a unique and efficient means of controlling the PPC effect in monolayer MoS₂. This PPC effect may offer novel functionalities for MoS₂-based optoelectronic applications in the future.
